



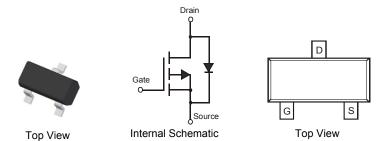
P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
 - $60m\Omega$ @ $V_{GS} = -4.5V$
 - $90m\Omega$ @ $V_{GS} = -2.5V$
 - $113m\Omega$ @ $V_{GS} = -1.8V$
- Low Input Capacitance
- Fast Switching Speed Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)



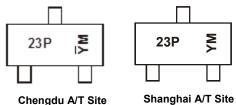
Ordering Information (Note 4&5)

Part Number	rt Number Qualification Case		Packaging	
DMP2305U-7	Standard	SOT23	3000/Tape & Reel	
DMP2305UQ-7	Automotive	SOT23	3000/Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



Shanghai A/T Site

23P = Product Type Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)

October 2013

Y or \overline{Y} = Year (ex: A = $2\overline{0}13$)

M = Month (ex: 9 = September)

Date Code Key

Year	200	9	2010		2011	20	12	2013		2014	2	2015
Code	W		Χ		Υ		7	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characte	eristic		Symbol	Value	Units
Drain-Source Voltage		V _{DSS}	-20	V	
Gate-Source Voltage		V _{GSS}	±8	V	
Continuous Drain Current (Note 6) Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			I _D	-4.2 -3.4	А
Pulsed Drain Current (Note 7)			I _{DM}	-10	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P_{D}	1.4	W
Thermal Resistance, Junction to Ambient @T _A = 25°C	$R_{\theta JA}$	90	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

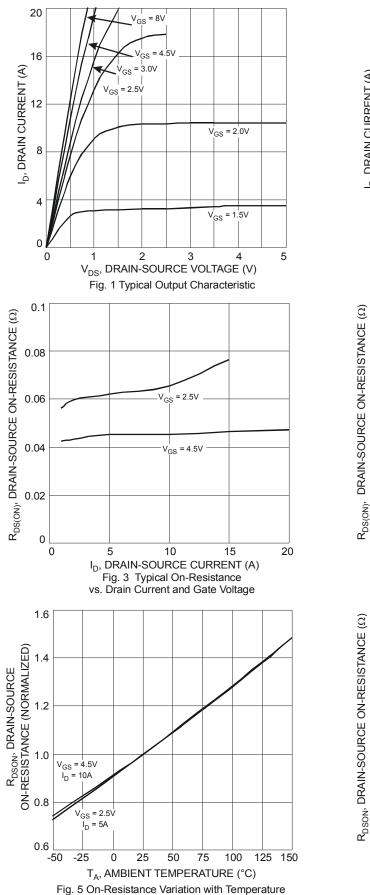
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

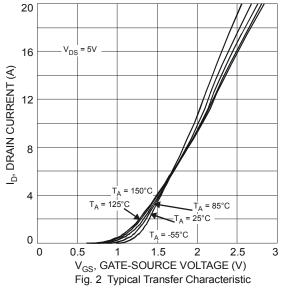
Characteristic	Symbol	Min	Tyn	Max	Unit	Test Condition	
	Symbol	IVIIII	Тур	IVIAX	Unit	rest Condition	
OFF CHARACTERISTICS (Note 8)			ı	ı		1	
Drain-Source Breakdown Voltage	BV _{DSS}	-20			V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_	_	-1.0	μA	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(th)}$	-0.5	-	-0.9	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			45	60		$V_{GS} = -4.5V$, $I_{D} = -4.2A$	
Static Drain-Source On-Resistance	R _{DS} (ON)	_	60	90	mΩ	$V_{GS} = -2.5V$, $I_{D} = -3.4A$	
	,		87	113		$V_{GS} = -1.8V$, $I_{D} = -2.0A$	
Forward Transfer Admittance	Y _{fs}	_	9	_	S	$V_{DS} = -5V, I_{D} = -4A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	727	_	pF	14 0014 14 014	
Output Capacitance	Coss	_	69	_	pF	$V_{DS} = -20V, V_{GS} = 0V$ -f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	64	_	pF	-1 = 1.0WH2	
Gate Resistance	R _G		23		Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz$	
SWITCHING CHARACTERISTICS							
Total Gate Charge	Qq		7.6	_	nC		
Gate-Source Charge	Q _{gs}	_	1.4	_	nC	$V_{GS} = -4.5V$, $V_{DS} = -4V$, $I_{D} = -3.5A$	
Gate-Drain Charge	Q_{gd}	_	1.2	_	nC		
Turn-On Delay Time	t _{D(on)}	_	14.0		ns		
Turn-On Rise Time	t _r	_	13.0	_	ns	$V_{DS} = -4V, V_{GS} = -4.5V,$	
Turn-Off Delay Time	t _{D(off)}	_	53.8		ns	$R_L = 4\Omega$, $R_G = 6\Omega$, $I_D = -1A$	
Turn-Off Fall Time	t _f	_	23.2	_	ns		

Notes:

- 6. Device mounted on FR-4 PCB with 2oz. Copper and test pulse width $t \le 10s$.
- Repetitive rating, pulse width limited by junction temperature.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.







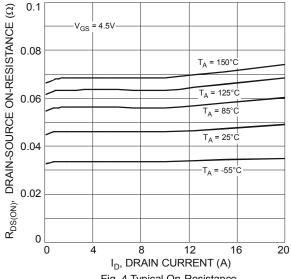


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

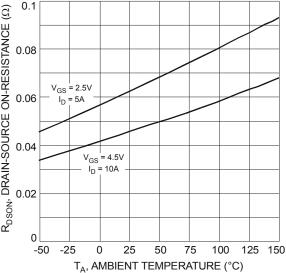


Fig. 6 On-Resistance Variation with Temperature



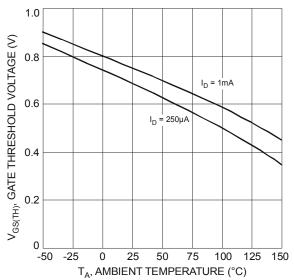
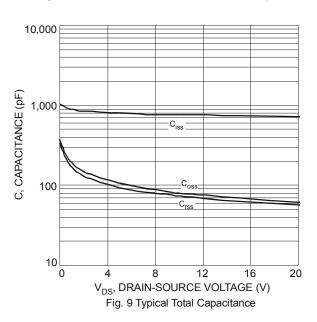
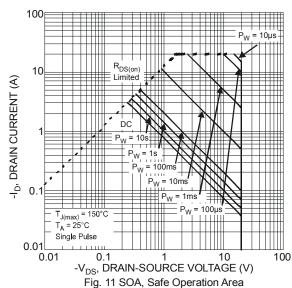
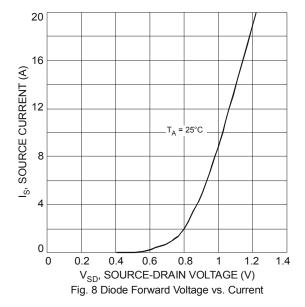


Fig. 7 Gate Threshold Variation vs. Ambient Temperature







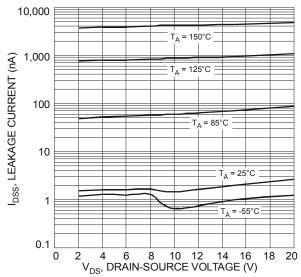
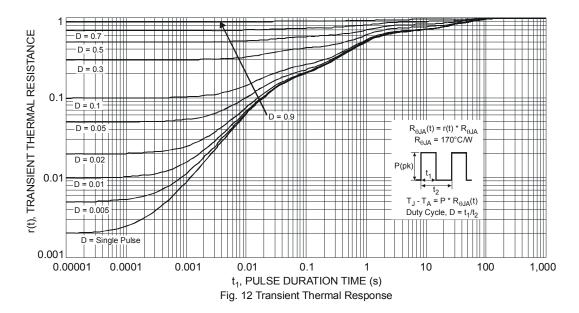


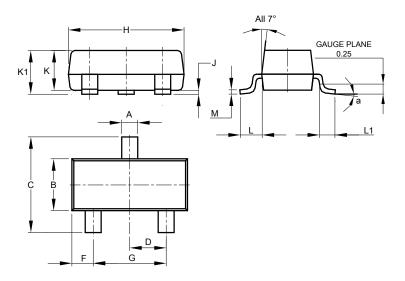
Fig. 10 Typical Leakage Current vs. Drain-Source Voltage





Package Outline Dimensions

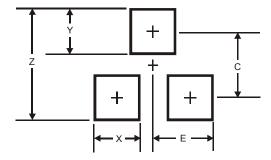
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT23							
Dim	Min	Min Max Ty						
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
M	0.085	0.150	0.110					
α	8°							
All Dimensions in mm								

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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